74LVC2G38

Dual 2-input NAND gate; open drain

Rev. 15 — 28 August 2023

Product data sheet

1. General description

The 74LVC2G38 is a dual 2-input NAND gate with open-drain outputs. Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in mixed 3.3 V and 5 V environments. Schmitt-trigger action at all inputs makes the circuit tolerant of slower input rise and fall times.

This device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the potentially damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- · 5 V tolerant outputs for interfacing with 5 V logic
- Overvoltage tolerant inputs to 5.5 V
- · High noise immunity
- CMOS low power dissipation
- I_{OFF} circuitry provides partial Power-down mode operation
- ±24 mA output drive (V_{CC} = 3.0 V)
- · Open-drain outputs
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Complies with JEDEC standard:
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8C (2.7 V to 3.6 V)
 - JESD36 (4.5 V to 5.5 V)
- ESD protection:
 - HBM: ANSI/ESDA/JEDEC JS-001 class 2 exceeds 2000 V
 - CDM: ANSI/ESDA/JEDEC JS-002 class C3 exceeds 1000 V
- · Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G38DP	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC2G38DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; SOT7 body width 2.3 mm	
74LVC2G38GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74LVC2G38GF	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1 × 0.5 mm	SOT1089
74LVC2G38GN	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm	SOT1116
74LVC2G38GS	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1.0 × 0.35 mm	SOT1203
74LVC2G38GX	-40 °C to +125 °C	X2SON8	plastic thermal enhanced extremely thin small outline package; no leads; 8 terminals; body 1.35 × 0.8 × 0.32 mm	SOT1233-2

4. Marking

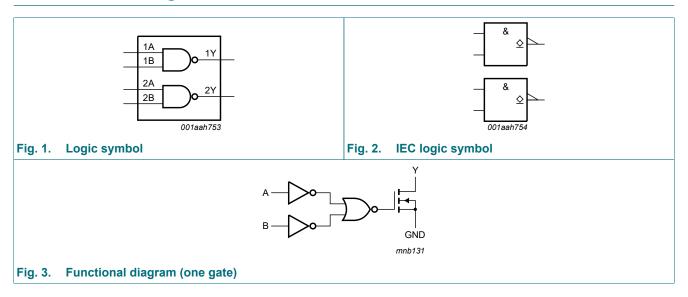
Table 2. Marking codes

and a state of the					
Type number	Marking code[1]				
74LVC2G38DP	Y38				
74LVC2G38DC	Y38				
74LVC2G38GT	Y38				
74LVC2G38GF	YB				
74LVC2G38GN	YB				
74LVC2G38GS	YB				
74LVC2G38GX	YB				

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

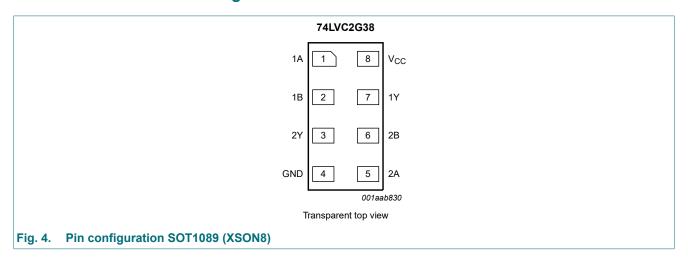
Dual 2-input NAND gate; open drain

5. Functional diagram

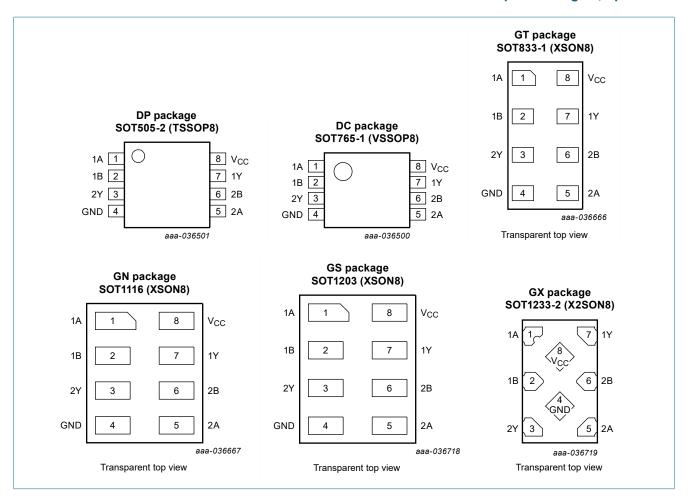


6. Pinning information

6.1. Pinning



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6.2. Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table

 $H = HIGH \text{ voltage level}; L = LOW \text{ voltage level}; Z = high-impedance OFF-state.}$

Input		Output
nA	nB	nY
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+6.5	V
VI	input voltage		[1]	-0.5	+6.5	V
Vo	output voltage	Active mode	[1]	-0.5	V _{CC} + 0.5	V
		Power-down mode; V _{CC} = 0 V	[1]	-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
I _{OK}	output clamping current	$V_O < 0 \text{ V or } V_O > V_{CC}$		-	±50	mA
Io	output current	V _O = 0 V to V _{CC}		-	±50	mA
I _{CC}	supply current			-	100	mA
I _{GND}	ground current			-100	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C				
		All packages except SOT1233-2	[2]	-	250	mW
		SOT1233-2 package	[3]	-	300	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For SOT765-1 (VSSOP8) package: Ptot derates linearly with 4.9 mW/K above 99 °C.

For SOT833-1 (XSON8) package: P_{tot} derates linearly with 3.1 mW/K above 68 °C.

For SOT1089 (XSON8) package: Ptot derates linearly with 4.0 mW/K above 88 °C.

For SOT1116 (XSON8) package: P_{tot} derates linearly with 4.2 mW/K above 90 °C.

For SOT1203 (XSON8) package: Ptot derates linearly with 3.6 mW/K above 81 °C.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	Active mode	0	V _{CC}	V
		disable mode	0	5.5	V
		Power-down mode; V _{CC} = 0 V	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	-	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	-	10	ns/V

^[2] For SOT505-2 (TSSOP8) package: Ptot derates linearly with 4.6 mW/K above 96 °C.

^[3] For SOT1233-2 (X2SON8) package: P_{tot} derates linearly with 7.7 mW/K above 118 °C.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T _{amb} = -4	0 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
	V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}	-	-	V	
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3 × V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I_O = 100 μ A; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	0.08	0.45	V
		I_{O} = 8 mA; V_{CC} = 2.3 V	-	0.14	0.3	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	0.19	0.4	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	0.37	0.55	V
		I_{O} = 32 mA; V_{CC} = 4.5 V	-	0.43	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±1	μΑ
I _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	±0.1	±2	μΑ
I _{OFF}	power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0 V	-	±0.1	±2	μΑ
I _{CC}	supply current	V _I = 5.5 V or GND; V _{CC} = 1.65 V to 5.5 V; I _O = 0 A	-	0.1	4	μΑ
ΔI _{CC}	additional supply current	per pin; V _I = V _{CC} - 0.6 V; V _{CC} = 2.3 V to 5.5 V; I _O = 0 A	-	5	500	μΑ
Cı	input capacitance		-	2.5	-	рF

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Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T _{amb} = -4	0 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3 × V _{CC}	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH}$ or V_{IL}				
		I _O = 100 μA; V _{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.70	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.60	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.80	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.80	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	±1	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	±0.1	±2	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 5.5 \text{ V}$; $V_{CC} = 0 \text{ V}$	-	-	±2	μΑ
I _{CC}	supply current	V _I = 5.5 V or GND; V _{CC} = 1.65 V to 5.5 V; I _O = 0 A	-	-	4	μΑ
ΔI _{CC}	additional supply current	per pin; V _I = V _{CC} - 0.6 V; V _{CC} = 2.3 V to 5.5 V; I _O = 0 A	-	-	500	μΑ

^[1] All typical values are measured at T_{amb} = 25 °C.

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11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see Fig. 6.

Symbol	Parameter	Conditions	-40	°C to +85 °	,C	-40 °C to +125 °C		Unit
			Min	Typ [1]	Max	Min	Max	
t _{PZL}	OFF-state to LOW	nA, nB to nY; see Fig. 5						
	propagation delay	V _{CC} = 1.65 V to 1.95 V	1.2	3.0	8.6	1.2	10.8	ns
		V _{CC} = 2.3 V to 2.7 V	0.7	1.8	4.8	0.7	6.0	ns
		V _{CC} = 2.7 V	0.7	2.5	4.4	0.7	5.5	ns
		V _{CC} = 3.0 V to 3.6 V	0.7	2.1	4.1	0.7	5.2	ns
		V _{CC} = 4.5 V to 5.5 V	0.5	1.5	3.3	0.5	4.2	ns
t _{PLZ}	LOW to OFF-state	nA, nB to nY; see Fig. 5						
	propagation delay	V _{CC} = 1.65 V to 1.95 V	1.2	3.0	8.6	1.2	10.8	ns
		V _{CC} = 2.3 V to 2.7 V	0.7	1.8	4.8	0.7	6.0	ns
		V _{CC} = 2.7 V	0.7	2.5	4.4	0.7	5.5	ns
		V _{CC} = 3.0 V to 3.6 V	0.7	2.1	4.1	0.7	5.2	ns
		V _{CC} = 4.5 V to 5.5 V	0.5	1.5	3.3	0.5	4.2	ns
C _{PD}	power dissipation capacitance	per gate; $V_I = GND$ to V_{CC} [2]	-	5	-	-	-	pF

[1] Typical values are measured at nominal V_{CC} and at T_{amb} = 25 °C.

[2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

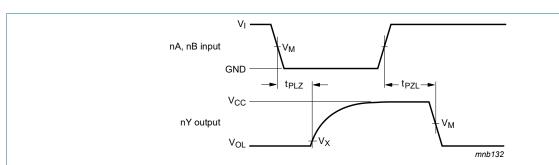
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs.}$

11.1. Waveforms and test circuit



Measurement points are given in Table 9

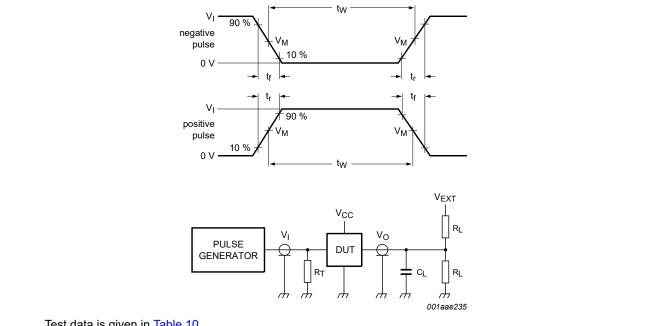
V_{OL} is a typical output voltage level that occurs with the output load.

Fig. 5. Inputs nA and nB to output nY propagation delay times

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Table 9. Measurement points

Supply voltage	Input	Output	Output		
V _{CC}	V _M	V _X	V _M		
1.65 V to 1.95 V	0.5 × V _{CC}	V _{OL} + 0.15 V	0.5 × V _{CC}		
2.3 V to 2.7 V	0.5 × V _{CC}	V _{OL} + 0.15 V	0.5 × V _{CC}		
2.7 V	1.5 V	V _{OL} + 0.3 V	1.5 V		
3.0 V to 3.6 V	1.5 V	V _{OL} + 0.3 V	1.5 V		
4.5 V to 5.5 V	0.5 × V _{CC}	V _{OL} + 0.3 V	0.5 × V _{CC}		



Test data is given in Table 10

Definitions for test circuit:

R_L = Load resistance;

C_L = Load capacitance including jig and probe capacitance;

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator;

 V_{EXT} = External voltage for measuring switching times;

Test circuit for measuring switching times Fig. 6.

Table 10. Test data

Supply voltage	Input		Load		V _{EXT}
V _{CC}	V _I	t _r , t _f	CL	R_L	t _{PLZ} , t _{PZL}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	2 × V _{CC}
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	30 pF	500 Ω	2 × V _{CC}
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	2 × V _{CC}

Product data sheet

Dual 2-input NAND gate; open drain

12. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

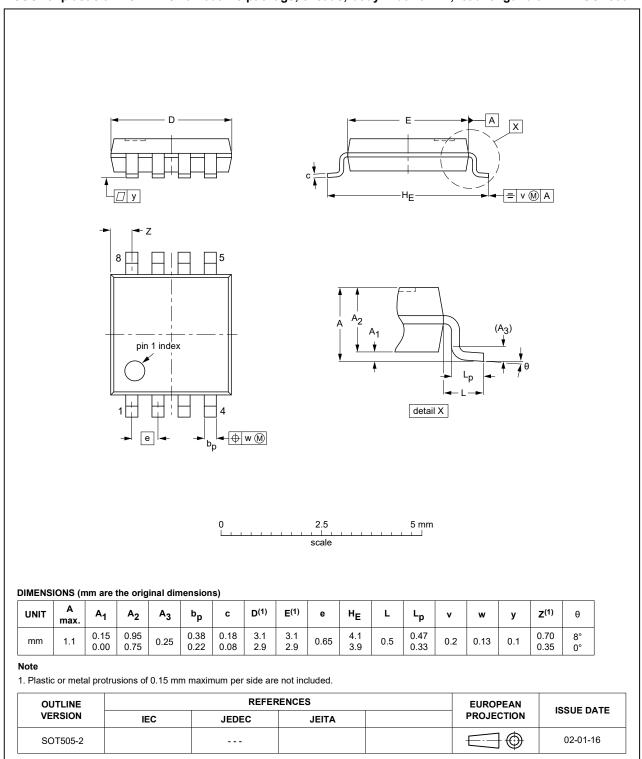


Fig. 7. Package outline SOT505-2 (TSSOP8)

Dual 2-input NAND gate; open drain

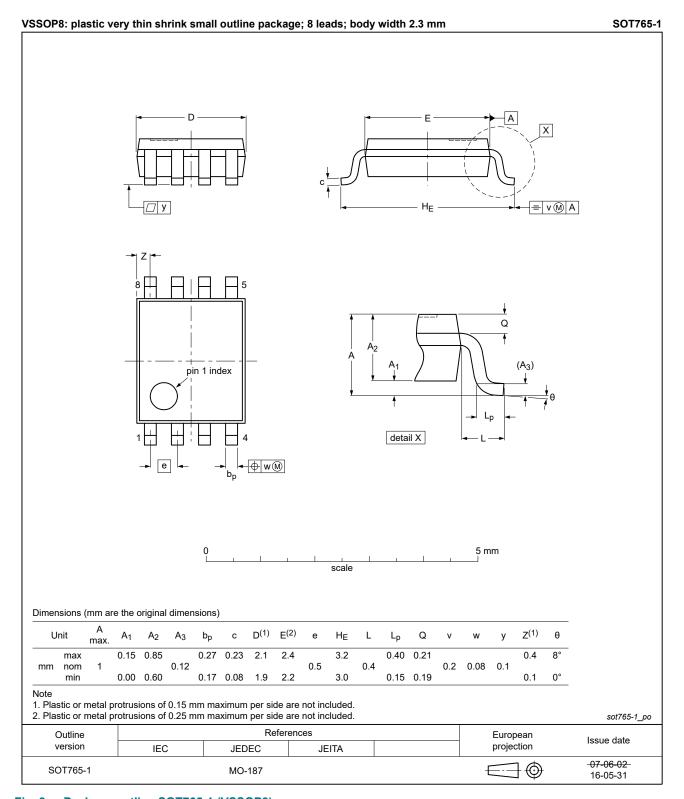


Fig. 8. Package outline SOT765-1 (VSSOP8)

Dual 2-input NAND gate; open drain

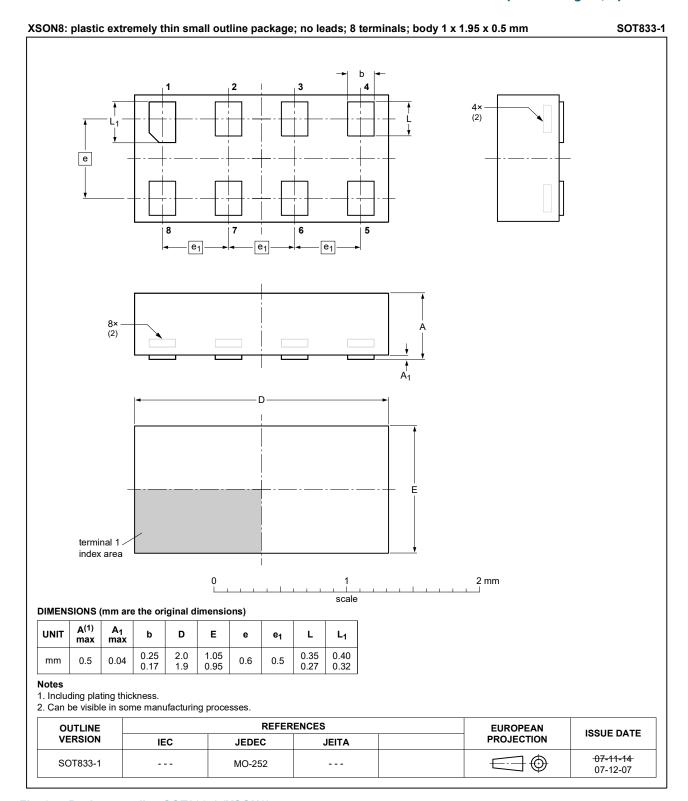


Fig. 9. Package outline SOT833-1 (XSON8)

Dual 2-input NAND gate; open drain

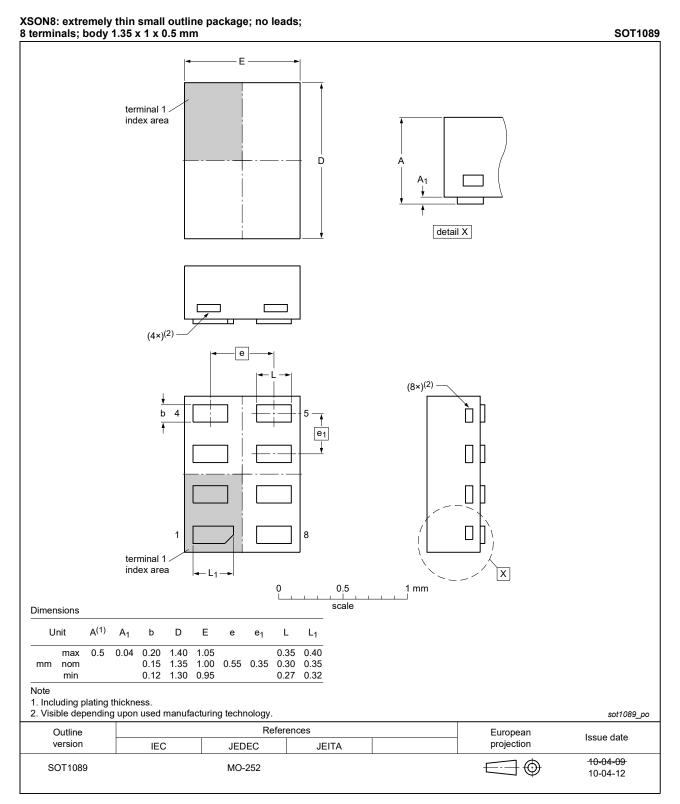


Fig. 10. Package outline SOT1089 (XSON8)

Dual 2-input NAND gate; open drain

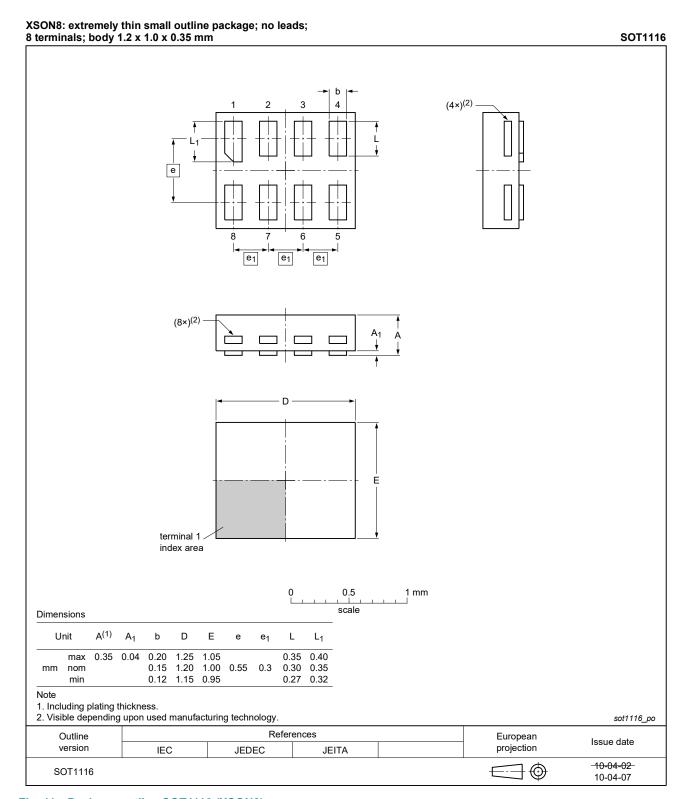


Fig. 11. Package outline SOT1116 (XSON8)

Dual 2-input NAND gate; open drain

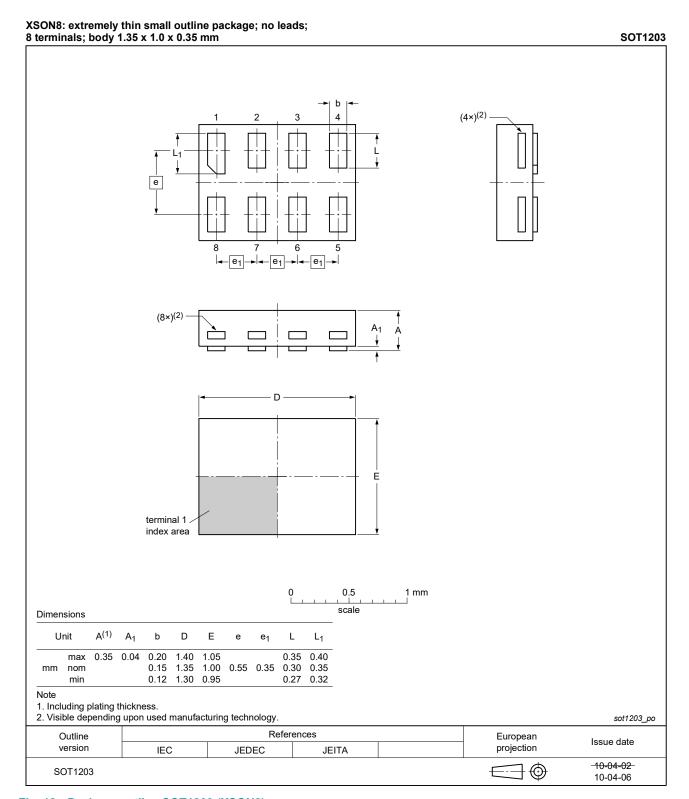


Fig. 12. Package outline SOT1203 (XSON8)

Dual 2-input NAND gate; open drain

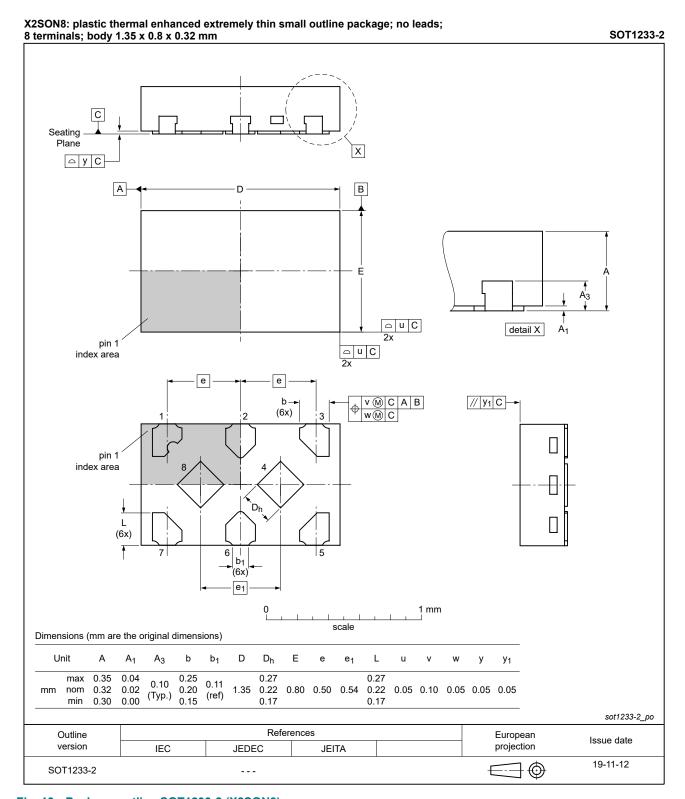


Fig. 13. Package outline SOT1233-2 (X2SON8)

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13. Abbreviations

Table 11. Abbreviations

Acronym	Description	
CDM	Charged Device Model	
CMOS	nplementary Metal-Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
НВМ	Human Body Model	
TTL	ransistor-Transistor Logic	

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74LVC2G38 v.15	20230828	Product data sheet	-	74LVC2G38 v.14		
Modifications:		COSTON 2. LOD opening apartical according to the latest OLD Lo standard.				
74LVC2G38 v.14	20220621	Product data sheet	-	74LVC2G38 v.13		
Modifications:	• SOT1233 (X	 Section 1 and Section 2 updated. SOT1233 (X2SON8) package changed to SOT1233-2 (X2SON8) package. Table 5: Ptot total power dissipation and derating values have been updated. 				
74LVC2G38 v.13	20170703	Product data sheet	-	74LVC2G38 v.12		
Modifications:	guidelines of Legal texts Added type	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Added type number 74LVC2G38GX (SOT1233 / X2SON8). Type number 74LVC2G38GD removed. 				
74LVC2G38 v.12	20161215	Product data sheet	-	74LVC2G38 v.11		
Modifications:	• <u>Table 7</u> : The	e maximum limits for leaka	ge current and su	pply current have changed.		
74LVC2G38 v.11	20130408	Product data sheet	-	74LVC2G38 v.10		
Modifications:	For type nu	For type number 74LVC2G38GD XSON8U has changed to XSON8.				
74LVC2G38 v.10	20120628	Product data sheet	-	74LVC2G38 v.9		
Modifications:	For type nu	For type number 74LVC2G38GM the SOT code has changed to SOT902-2.				
74LVC2G38 v.9	20111128	Product data sheet	-	74LVC2G38 v.8		
Modifications:	Legal pages	s updated.				
74LVC2G38 v.8	20101104	Product data sheet	-	74LVC2G38 v.7		
74LVC2G38 v.7	20090320	Product data sheet	-	74LVC2G38 v.6		
74LVC2G38 v.6	20080219	Product data sheet	-	74LVC2G38 v.5		
74LVC2G38 v.5	20070904	Product data sheet	-	74LVC2G38 v.4		
74LVC2G38 v.4	20060516	Product data sheet	-	74LVC2G38 v.3		
74LVC2G38 v.3	20050201	Product specification	-	74LVC2G38 v.2		
74LVC2G38 v.2	20041018	Product specification	-	74LVC2G38 v.1		
74LVC2G38 v.1	20031027	Product specification	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Dual 2-input NAND gate; open drain

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